



**S/N 09/470,265**

# PATENT

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Applicant: Karl M. Robinson                                  Examiner: Thien Tran  
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Title: DEVICES HAVING IMPROVED CAPACITANCE AND METHODS OF  
THEIR FABRICATION

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19. (Amended) A capacitor, comprising:  
a first conductive capacitor plate of a first material;  
a second conductive capacitor plate; and  
[a dielectric interposed between said first and second conductive capacitor plates, wherein said dielectric is an oxide of] a metal layer of a second material overlying the first conductive capacitor plate, wherein the metal layer includes a non-oxidized portion and an oxidized portion, wherein the oxidized portion is a dielectric of the capacitor.
20. (Amended) A memory system, comprising:  
a monolithic memory device, comprising a capacitor, wherein the capacitor comprises:  
a first conductive capacitor plate;